Thermodynamics of materials 18. Chemical potentials of Atomic Defects I

> Kunok Chang kunok.chang@khu.ac.kr

> > Kyung Hee University

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Chemical Potentials of Atomic Defects

• Chemical Potentials of Vacancies in Elemental Crystals



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Thermodynamics

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Thermodynamics

- A crystal at finite temperatures always contains a certain amount of point defects under equilibrium.
- The driving force of the formation of the defects is increase in the entropy. Defects usually plays significant role in determining properties of materials.



• The most common type of defects in a crystal are atomic vacancies, i.e., lattice sites with atoms missing.

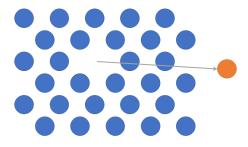


Figure: Creation of a vacancy by moving an atom from inside to the crystal surface.



• Because the creation of vacancies breaks the atomic bonds, the energy of the crystal interfaces. We define the formation energy of a vacancy as the energy increase in the system due to the creation of the vacancy while keeping the total number of atoms *n* in the crystal the same,

$$\Delta u_v = U_{n+v} - U_n$$

• The formation enthalpy of a vacancy, Δh_v , is defined as the enthalpy change by removing an atom inside a cystal and placing it on the surface

$$\Delta h_v = H_{n+v} - H_n = \Delta u_v + p \Delta v_v$$

where p is pressure and Δv_v is the vacancy formation volume.

 $\bullet\,$ The formation entropy of a vacancy, ΔS consists of two terms,

- Vibrational entropy Δs_v
- Configurational entropy ΔS_c

where

$$\Delta s_v = -k_{\mathsf{B}} \sum_i \ln \frac{\omega_i'}{\omega_i^{\circ}}$$

where ω_i' is the vibrational frequencies of atoms in a crystal with a vacancy, ω_i° is the vibrational frequencies of atoms in a perfect crystal. And

$$\Delta S_c = k_{\mathsf{B}} \ln \Omega = k_{\mathsf{B}} \ln \frac{(n+n_v)!}{n!n_v!}$$

where $n + n_v$ total lattice sites and n_v vacancies and n atoms.

• The free energy of the system is

$$G = G^{\circ} + n_v \Delta h_v - T\left(n_v \Delta s_v + k_{\mathsf{B}} \ln \frac{(n+n_v)!}{n!n_v!}\right)$$

where G° is the free energy of a perfect crystal.

• Using the Stirling approximation, we have

$$G = G^{\circ} + n_v \Delta g_v - k_{\mathsf{B}} T \Big[(n + n_v) \ln (n + n_v) - n \ln n - n_v \ln n_v \Big]$$

where

$$\Delta g_v = \Delta h_v - T \Delta s_v$$

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• The chemical potential of vacancies is then

$$\mu_{v} = \left(\frac{\partial G}{\partial n_{v}}\right)_{T,p,n}$$
$$= \Delta g_{v} + k_{\mathsf{B}}T \ln\left(\frac{n_{v}}{n+n_{v}}\right) = \Delta g_{v} + k_{\mathsf{B}}T \ln x_{v}$$

• At equilibrium

$$\mu_v = \Delta g_v + k_{\mathsf{B}} T \ln \left(\frac{n_v^{\circ}}{n + n_v^{\circ}} \right) = 0$$

by rearrangement,

$$\frac{n_v^{\circ}}{n+n_v^{\circ}} = x_v^{\circ} = \exp\left(-\frac{\Delta g_v}{k_{\rm B}T}\right)$$

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• Therefore, at equilibrium,

$$\mu_v = \mu_v^\circ + k_\mathsf{B} T \ln x_v^\circ = 0$$

• Under non-equilibrium conditions, e.g., a crystal under irradiation

$$\mu_v = \mu_v^\circ + k_{\mathsf{B}}T\ln x_v = k_{\mathsf{B}}T\ln\left(\frac{x_v}{x_v^\circ}\right)$$

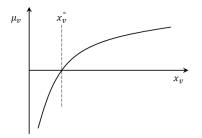


Figure: Chemical potential of vacancy as a function of vacancy concentration.

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Suppose a reaction,

$$\mathsf{A}_\mathsf{A} \leftrightarrow \mathsf{A}_\mathsf{S} + \mathsf{V}_\mathsf{A}$$

where A_A represents an A atom occupying an A lattice site inside a crystal, A_S represents an A atom occupying a surface site, and V_A represents a vacant site on the A lattice.

• Ignoring difference between A_A and A_S,

 $\mathsf{Null} \leftrightarrow \mathsf{V}_\mathsf{A}$

• Therefore, at equilibrium,

$$\mu_{\mathsf{Null}} = 0 = \mu_v$$

with assumption of ideal solution,

$$\mu_v = \mu_v^\circ + k_\mathsf{B} T \ln x_v$$

• For another reaction,

$$\mathsf{A}_\mathsf{A} \leftrightarrow \mathsf{V}_\mathsf{A} + \mathsf{A}_\mathsf{res}$$

or

$$\mathsf{Null} \leftrightarrow \left(\mathsf{V}_\mathsf{A} - \mathsf{A}_\mathsf{A}\right) + \mathsf{A}_\mathsf{res}$$

where A_{res} represents an A atom in a pure A atom reservoir, and their chemical potential is μ_A° .

• If the total number of lattice sites N is fixed,

$$\mu_{(\mathsf{V}_{\mathsf{A}}-\mathsf{A}_{\mathsf{A}})} = \mu_{(\mathsf{V}_{\mathsf{A}}-\mathsf{A}_{\mathsf{A}})}^{\circ} + k_{\mathsf{B}}T\ln\left(\frac{n_{v}}{N-n_{v}}\right) \tag{1}$$

\$\mu_{(V_A-A_A)}^{\circ}\$: Difference between \$n-1\$ atoms + 1 vacancy and perfect crystal of \$n\$ atoms.

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• Solving Eq.(1) for n_v ,

$$n_v = \frac{N}{1 + \exp\left(\frac{\mu_{(\mathbf{V}_{\mathbf{A}} - \mathbf{A}_{\mathbf{A}})}^{\circ} - \mu_{(\mathbf{V}_{\mathbf{A}} - \mathbf{A}_{\mathbf{A}})}}{k_{\mathbf{B}}T}\right)}$$

• At equilibrium, we have

$$\mu_{(\mathsf{V}_\mathsf{A}-\mathsf{A}_\mathsf{A})}+\mu_\mathsf{A}^\circ=0$$

if the total number of lattice sites N is fixed,

$$\mu_{(\mathsf{V}_\mathsf{A}-\mathsf{A}_\mathsf{A})}^\circ + k_\mathsf{B}T\ln\left(\frac{n_v}{N-n_v}\right) + \mu_\mathsf{A}^\circ = 0$$

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• If the total number of lattice sites N is fixed,

$$n_v^{\circ} = \frac{N}{1 + \exp\left(\frac{\mu_{(\mathbf{V}_{\mathbf{A}} - \mathbf{A}_{\mathbf{A}})}^{\circ} + \mu_{\mathbf{A}}^{\circ}}{k_{\mathbf{B}}T}\right)}$$

• For very small vacancy concentrations,

$$x_v^{\circ} = \frac{n_v^{\circ}}{N} = \exp\left(-\frac{\mu_{(\mathsf{V}_\mathsf{A}-\mathsf{A}_\mathsf{A})}^{\circ} + \mu_\mathsf{A}^{\circ}}{k_\mathsf{B}T}\right)$$

therefore, we have

$$\mu_v^\circ = \Delta g_v = \mu_{(\mathsf{V}_\mathsf{A} - \mathsf{A}_\mathsf{A})}^\circ + \mu_\mathsf{A}^\circ$$

or

$$\mu_{(\mathsf{V}_{\mathsf{A}}-\mathsf{A}_{\mathsf{A}})}^{\circ}=\mu_{v}^{\circ}-\mu_{\mathsf{A}}^{\circ}$$

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